

IN THE CLAIMS

Please cancel non-elected claim 33 without prejudice.

Please amend the following claims and add new claims 34-46.

32. (Currently Amended) A method of cleaning a wafer comprising:
spinning a wafer;
exposing said spinning wafer to an etchant or cleaning chemicals;
after exposing said wafer to said etchant or cleaning chemical and
prior to dispensing DI water on said etchant or cleaning chemical covered wafer
exposing said spinning wafer to a liquid or vapor having a lower surface tension
than water.

33. (Canceled)

34. (New) The method of claim 32 further comprising applying
megasonics energy to said wafer while exposing said wafer to said cleaning
chemicals or etchants.

35. (New) The method of claim 34 further comprising after exposing said
wafer to said liquid or vapor having a lower surface tension than water, rinsing said
wafer with said DI water.

36. (New) The method of claim 35 further comprising applying
megasonics energy to said wafer while rinsing said wafer.

37. (New) A method of rinsing chemicals or etchants from a wafer
comprising:

rotating a wafer;
dispensing cleaning chemicals or etchants onto said wafer to form an etchant or chemical covered wafers;
immediately after dispensing said cleaning chemicals or etchants onto said rotating wafer, applying a liquid or vapor having a lower surface tension than water onto said cleaning chemical or etchant covered wafer; and
immediately after applying said liquid or vapor having a lower surface tension than water, dispensing rinse water onto said spinning wafer.

38. (New) The method of claim 37 further comprising heating said rinse water prior to dispensing said rinse water on said wafer.

39. (New) The method of claim 38 wherein said rinse water is heated to a temperature between 60-70°C.

40. (New) The method of claim 37 further comprise applying megasonics energy to said wafer while dispensing said rinse water onto said wafer.

41. (New) The method of claim 37 further comprising stopping said dispensing of said rinse water and spinning said wafer dry.

42. (New) A method of cleaning or etching a wafer comprising:
placing a wafer on a support over a plate having a plurality of transducers formed thereon, wherein said wafer is horizontally supported and separated by a gap from said plate;
flowing a liquid in said gap between said wafer and said support;
dispensing chemicals or etchants onto said wafer to form a chemical or etchant covered wafer while flowing said liquid in said gap;

after dispensing said chemicals or said etchant, and prior to dispensing Di water on said chemical or etchant covered wafer, dispensing a liquid or vapor having a lower surface tension than water onto said chemical or etchant covered wafer; and

after applying said vapor or liquid, dispensing rinse water onto said spinning wafer.

43. (New) The method of claim 42 further comprising applying megasonics energy to said wafer from said transducers while said dispensing of said chemical or said etchant.

44. (New) The method of claim 42 further comprising heating said rinse water prior to applying said rinse water onto said wafer.

45. (New) The method of claim 44 wherein said rinse water is heated to a temperature between 60-70°C.

46. (New) The method of claim 42 further comprising flowing said a liquid into said gap between said wafer and said support, and applying megasonics energy to said wafer from said transducer while dispensing said rinse water onto said wafer.